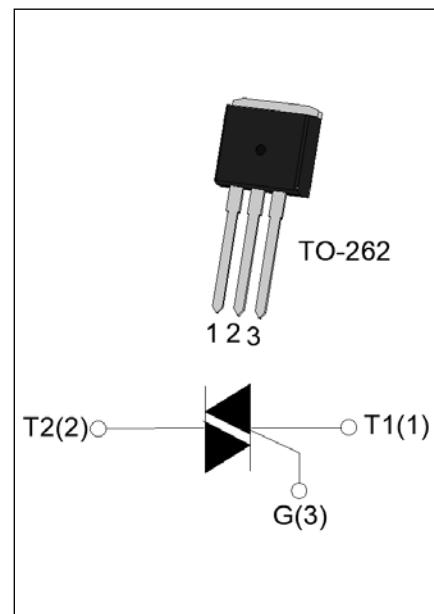


**DESCRIPTION:**

The JST139D-800D triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-262 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(\text{RMS})}$	16	A
$V_{\text{DRM}} / V_{\text{RRM}}$	800	V
$I_{G(T_{I/II/III/IV})}$	5/5/5/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leqslant 95^\circ\text{C}$)	$I_{T(\text{RMS})}$	16	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	140	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		154	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	98	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	I - II III-IV	50 20	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(\text{AV})}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive,off-state;FIG.7)	V_{pp}	4.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX.	5	mA
		IV		10	
V_{GT}	ALL		MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX.	15	mA
		II		20	
I_H	$I_T=500\text{mA}$		MAX.	10	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	40	V/ μs
$(dV/dt)c$	$(dI/dt)c=7.2\text{A/ms}$, $T_j=110^\circ\text{C}$		MIN.	2	V/ μs
t_{on}	$I_G=20\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	3	μs	
			50		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=15\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5 V
V_{TO}	Threshold voltage		$T_j=125^\circ\text{C}$	0.75 V
R_D	Dynamic resistance		$T_j=125^\circ\text{C}$	27 m Ω
I_{DRM}	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5 μA
I_{RRM}			$T_j=125^\circ\text{C}$	0.5 mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.3	°C/W
$R_{th(j-a)}$	junction to ambient (AC)	60	°C/W

ORDERING INFORMATION

J	ST	139	D	-800	D
JieJie Microelectronics Co., Ltd.					
	Triacs				
		<u>I_T(RMS):16A</u>			
			D:TO-262		
				<u>800:V_{DRM} / V_{RRM} ≥ 800V</u>	
					<u>D:IGT1-3 ≤ 5mA IGT4 ≤ 10mA</u>

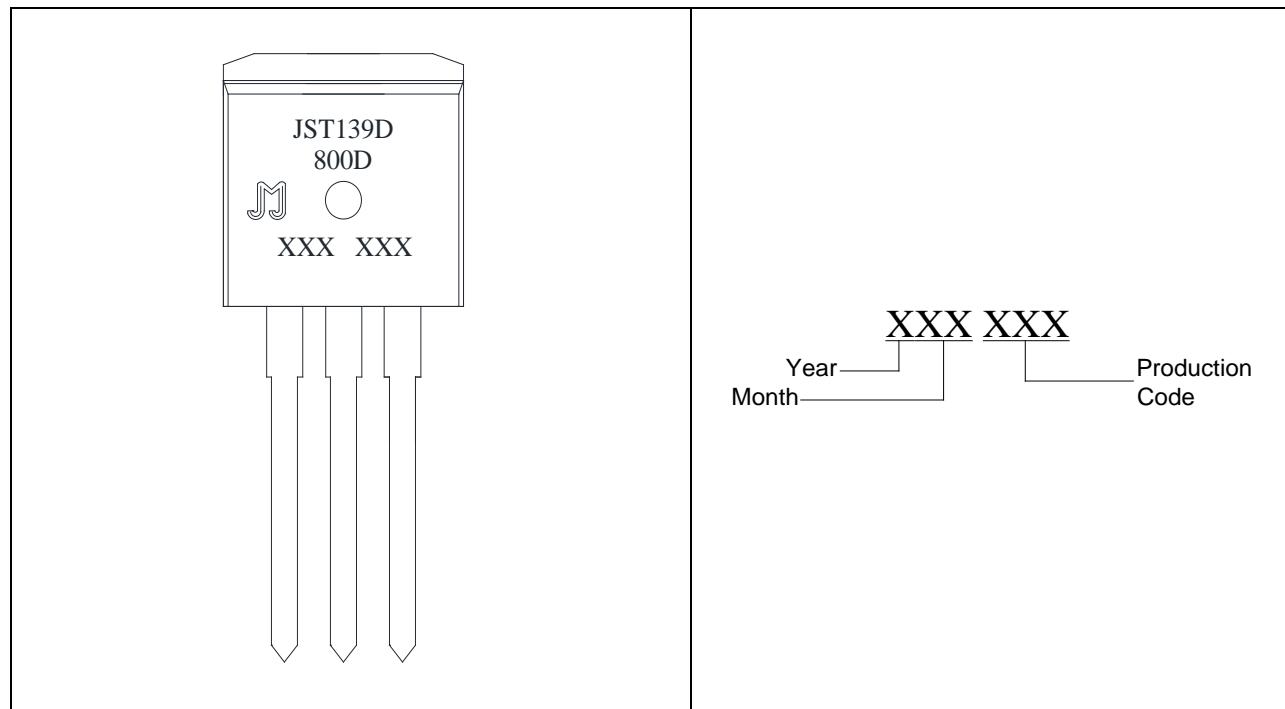
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

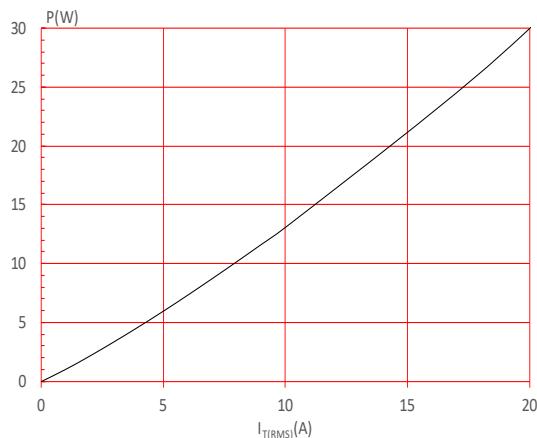


FIG.3: Surge peak on-state current versus number of cycles

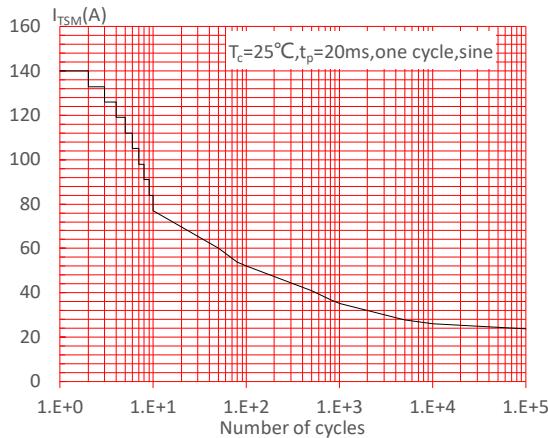


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t
(I - II : $dl/dt < 50\text{A}/\mu\text{s}$; III - IV : $dl/dt < 20\text{A}/\mu\text{s}$)

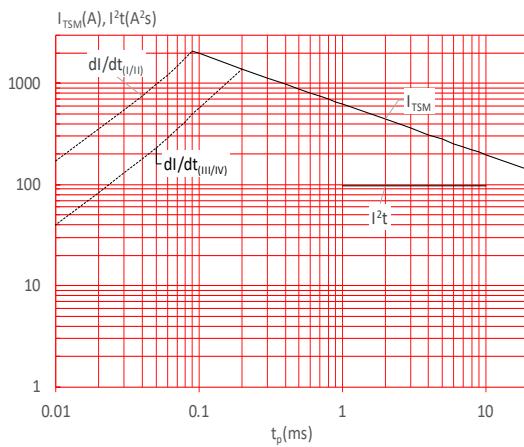


FIG.2: RMS on-state current versus case temperature

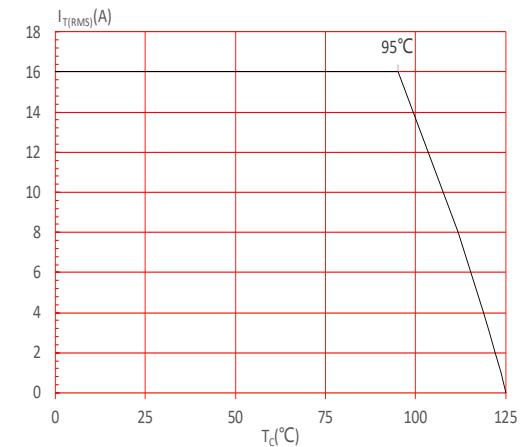


FIG.4: On-state characteristics

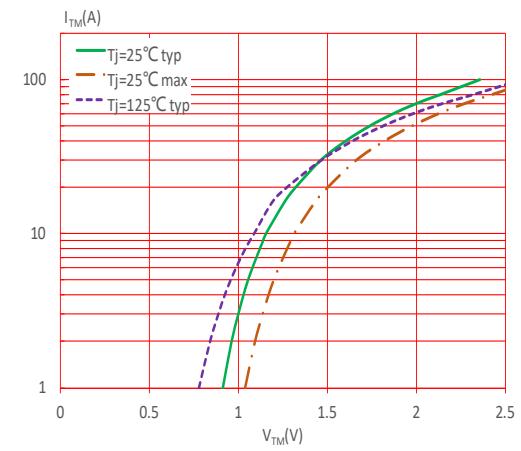


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

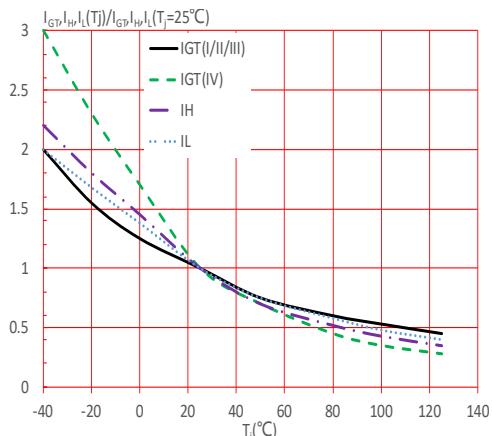
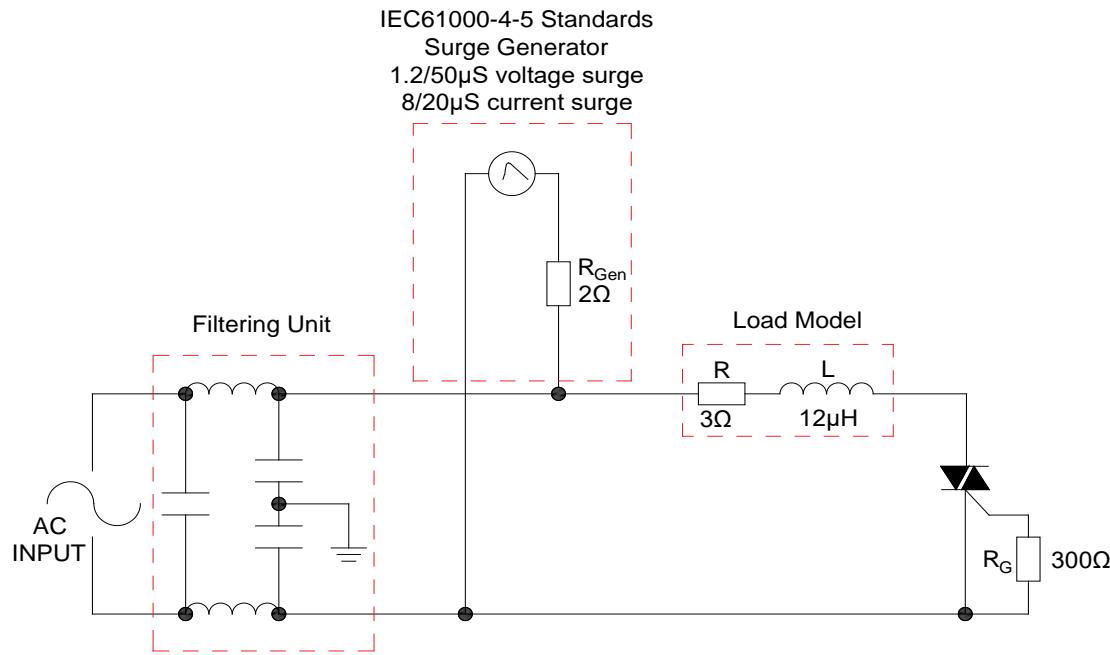


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

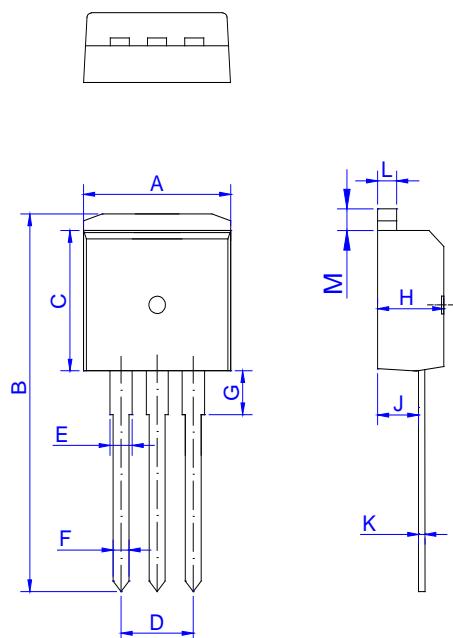
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I - II - III	IV			
JST139D-800D	800	5	10	TO-262	50	Tube

Document Revision History

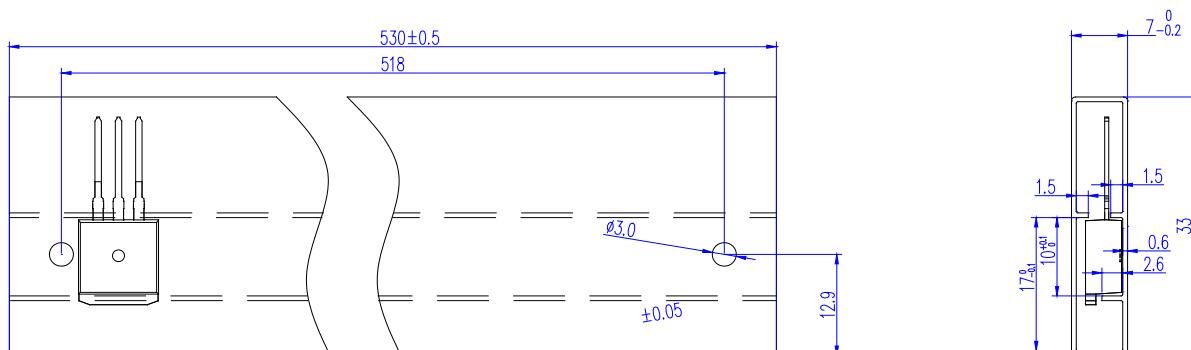
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.95		10.20	0.392		0.402
B	23.85		24.05	0.939		0.947
C	9.40		9.60	0.370		0.378
D	4.95		5.25	0.195		0.207
E	1.35		1.40	0.053		0.055
F	0.80		0.85	0.031		0.033
G	2.70		3.40	0.106		0.134
H	4.45		4.55	0.175		0.179
J	2.20		2.60	0.087		0.102
K	0.48		0.52	0.019		0.020
L	1.30		1.35	0.051		0.053
M	1.20		1.50	0.047		0.059

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-262	TUBE	50	1,000	5,000

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